优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- BV_{CEO} > 125V
- I_C = 1A high Continuous Collector Current
- I_{CM} = 3A Peak Pulse Current
- $R_{CE(sat)}$ = 160mΩ for a low equivalent On-Resistance
- 625mW Power dissipation
- h_{FE} specified up to 3A for high current gain hold up

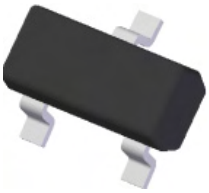
Mechanical Data

- Case: SOT23
- Case Material: molded plastic, “Green” molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Weight 0.008 grams (approximate)

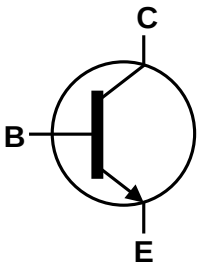
Applications

- DC-DC / DC-AC Modules
- Regulator
- LED driver
- CCFL Backlighting Inverters

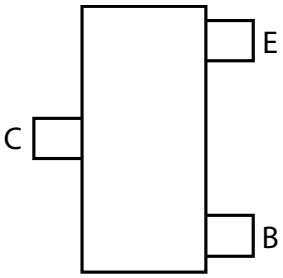
SOT23



Top View



Device Symbol



Top View
Pin-Out

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	125	V
Collector-Emitter Voltage	V_{CEO}	125	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current (Note 5)	I_{CM}	3	A
Base Current	I_B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

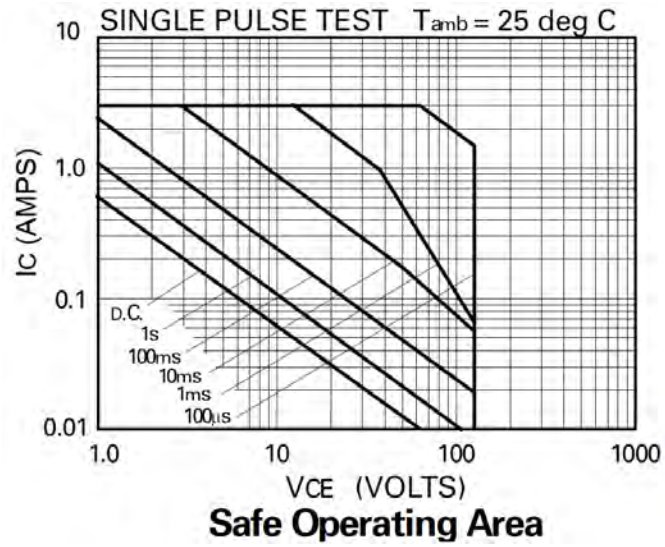
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	625	mW
Power Dissipation (Note 6)	P_D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{\theta JL}$	194	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

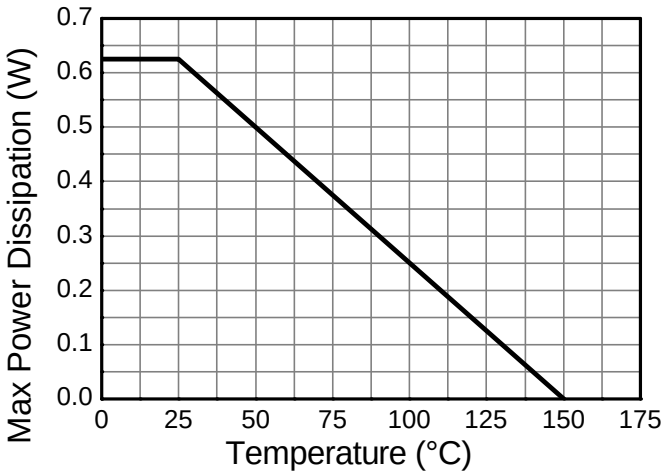
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

Notes:
5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Same as note 5, except the device is measured at t ≤ 5 sec.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

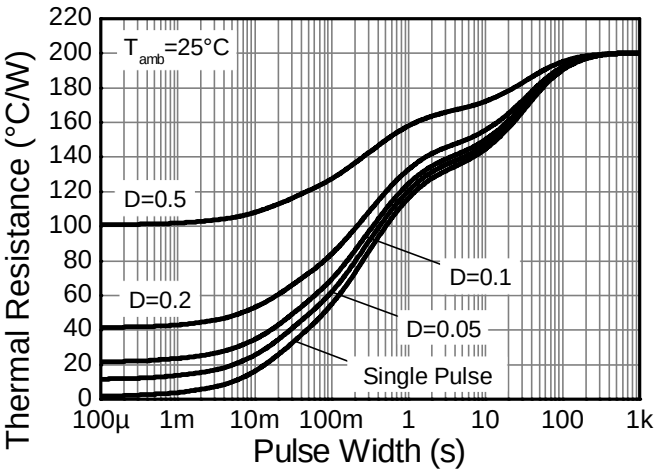
Thermal Characteristics and Derating information



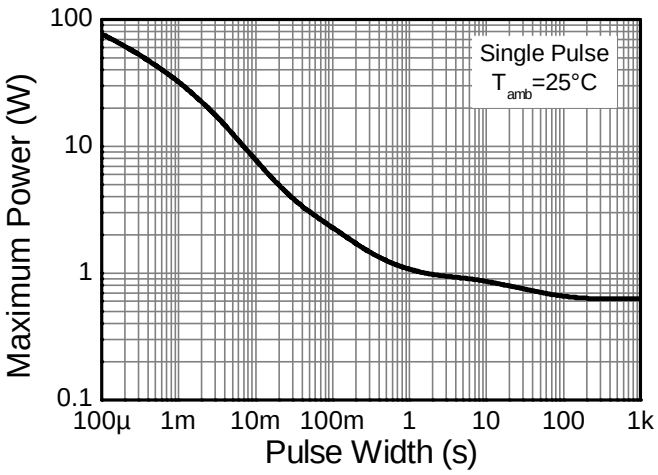
Safe Operating Area



Derating Curve



Transient Thermal Impedance



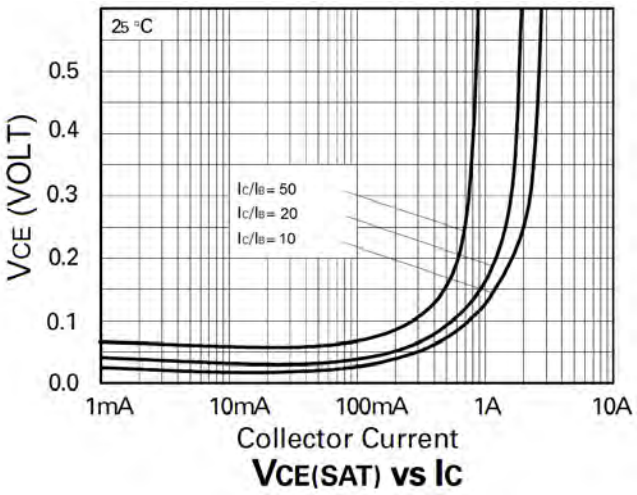
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

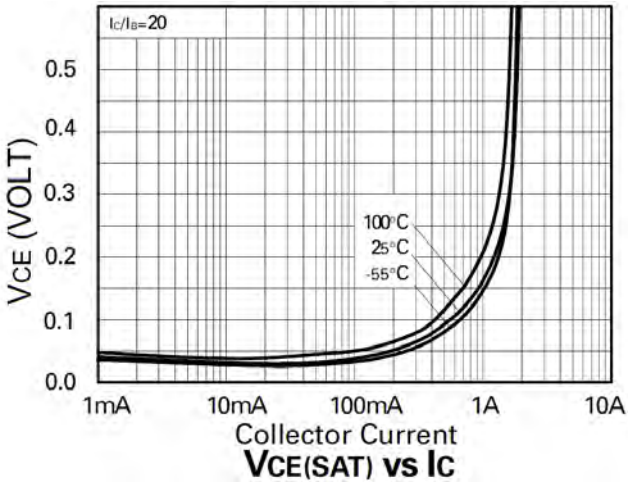
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	125	250	-	V	I_C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	125	160	-	V	I_C = 1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.3	-	V	I_E = 100μA
Collector Cut-off Current	I_{CBO}	-	<10	100	nA	V_{CB} = 100V
Emitter Cut-off Current	I_{EBO}	-	<10	100	nA	V_{EB} = 6.0V
Collector Emitter Cut-off Current	I_{CES}	-	<10	100	nA	V_{CES} = 100V
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	200 300 100 -	400 450 140 18	- - - -	-	I_C = 10mA, V_{CE} = 10V I_C = 200mA, V_{CE} = 10V I_C = 1A, V_{CE} = 10V I_C = 3A, V_{CE} = 10V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	- - - -	26 70 160 165	50 150 220 250	mV	I_C = 0.1A, I_B = 10mA I_C = 0.5A, I_B = 50mA I_C = 0.5A, I_B = 10mA I_C = 1A, I_B = 50mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	0.85	1.0	V	I_C = 1A, I_B = 50mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(on)}$	-	0.70	1.0	V	I_C = 1A, V_{CE} = 10V
Transition Frequency	f_T	100	155	-	MHz	I_C = 50mA, V_{CE} = 10V, f = 100MHz
Collector Output Capacitance	C_{obo}	-	7	15	pF	V_{CB} = 10V, f = 1MHz
Turn-On Time	$t_{(on)}$	-	60	-	ns	V_{CC} = 50V, I_C = 0.5A, I_{B1} = -I_{B2} = 50mA
Turn-Off Time	$t_{(off)}$	-	1300	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

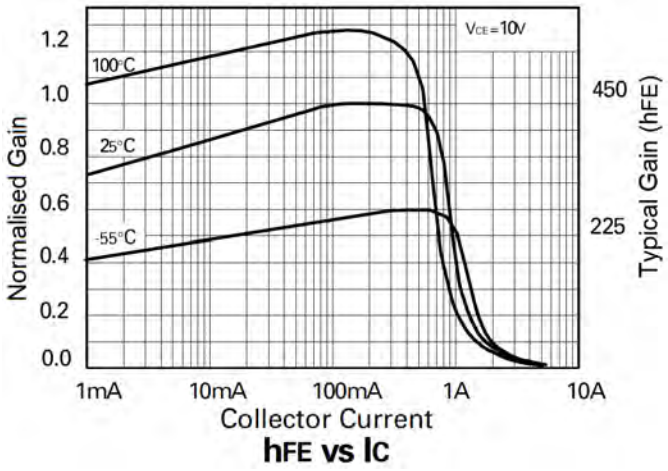
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



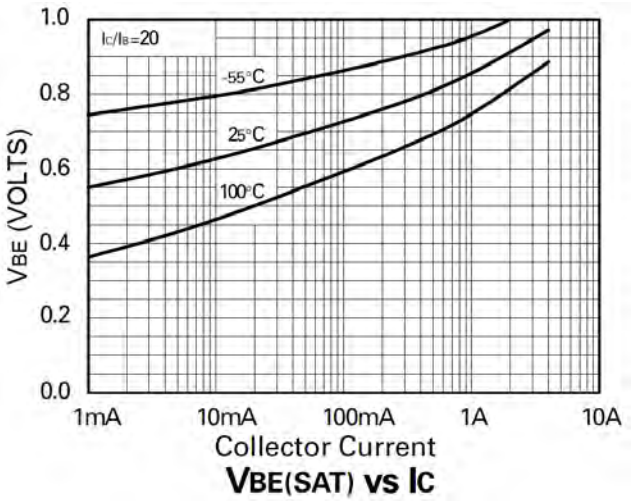
VCE(SAT) vs IC



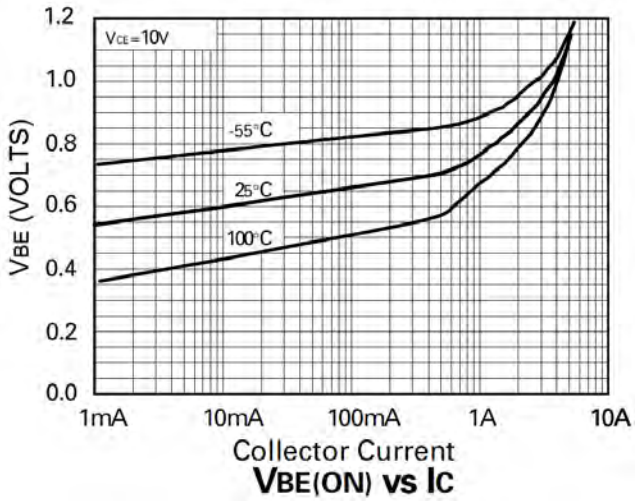
VCE(SAT) vs IC



hFE vs IC

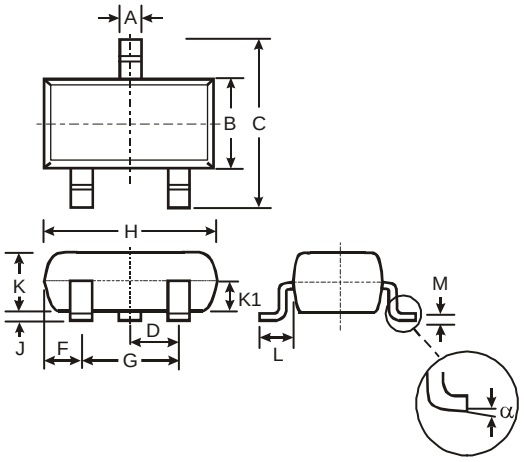


VBE(SAT) vs IC



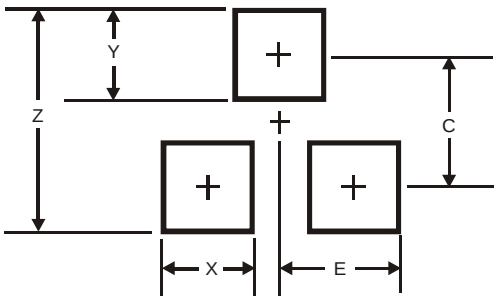
VBE(ON) vs IC

Package Outline Dimensions



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35